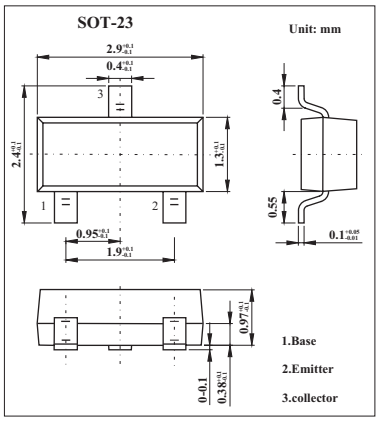
Medium Power Transistor
2SA1036K



Features

- Large I_C. $I_{CMax.}$ = -500mA
- Low $V_{CE(sat)}$. Ideal for low-voltage operation.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-40	V
Collector-emitter voltage	V_{CEO}	-32	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current *	I_C	-0.5	A
Collector power dissipation	P_C	0.2	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* P_C max. must not be exceeded.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C = -100 μA	-40			V
Collector-emitter breakdown voltage	V_{CEO}	I_C = -1 mA	-32			V
Emitter-base breakdown voltage	V_{EBO}	I_E = -100 μA	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -20 V			-1	μ A
Emitter cutoff current	I_{EBO}	V_{EB} = -4 V			-1	μ A
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -100 mA, I_B = -10 mA			-0.4	V
DC current gain	h_{FE}	V_{CE} = -3 V, I_C = -10mA	82		390	
Output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0A, f = 1MHz		7		pF
Transition frequency	f_T	V_{CE} = -5 V, I_E = 20 mA, f = 100MHz		200		MHz

h_{FE} Classification

Marking	HP	HQ	HR
Rank	P	Q	R
hFE	82～180	120～270	180～390